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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	16
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 9x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l011f4p6tr

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3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

The BOOT0 pin is shared with PB9 GPIO pin. This pin is an input-only pin. If nBOOT_SEL option bit is reset, sampling this pin on NRST rising edge gives the internal BOOT0 state. This pin then works as PB9 pin. The input voltage characteristics of this pin are specific for BOOT0 pin type (see [Table 50: I/O static characteristics](#)).

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event

3.10 Analog-to-digital converter (ADC)

A native 12-bit, extended to 16-bit through hardware oversampling, analog-to-digital converter is embedded into STM32L011x3/4 devices. It has up to 10 external channels and 2 internal channels (temperature sensor, voltage reference). Three channels, PA0, PA4 and PA5, are fast channels, while the others are standard channels.

The ADC performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of 1.14 MSPS even with a low CPU speed. The ADC consumption is low at all frequencies (~25 μ A at 10 kSPS, ~200 μ A at 1MSPS). An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

3.11 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value.

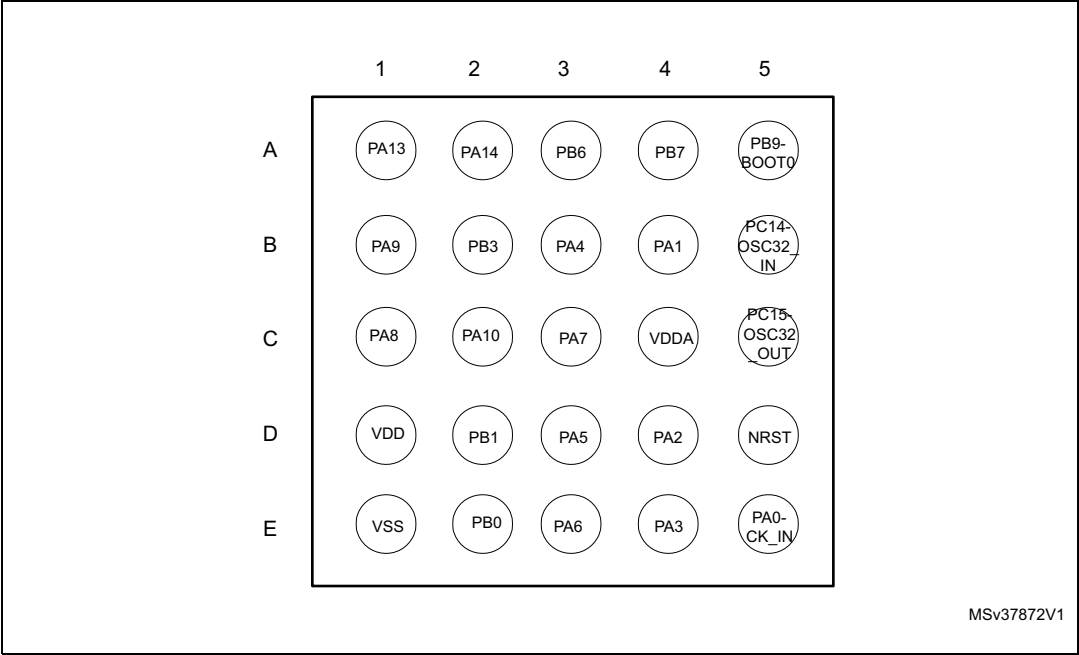
The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode (see [Table 57: Temperature sensor calibration values](#)).

3.11.1 Internal voltage reference (V_{REFINT})

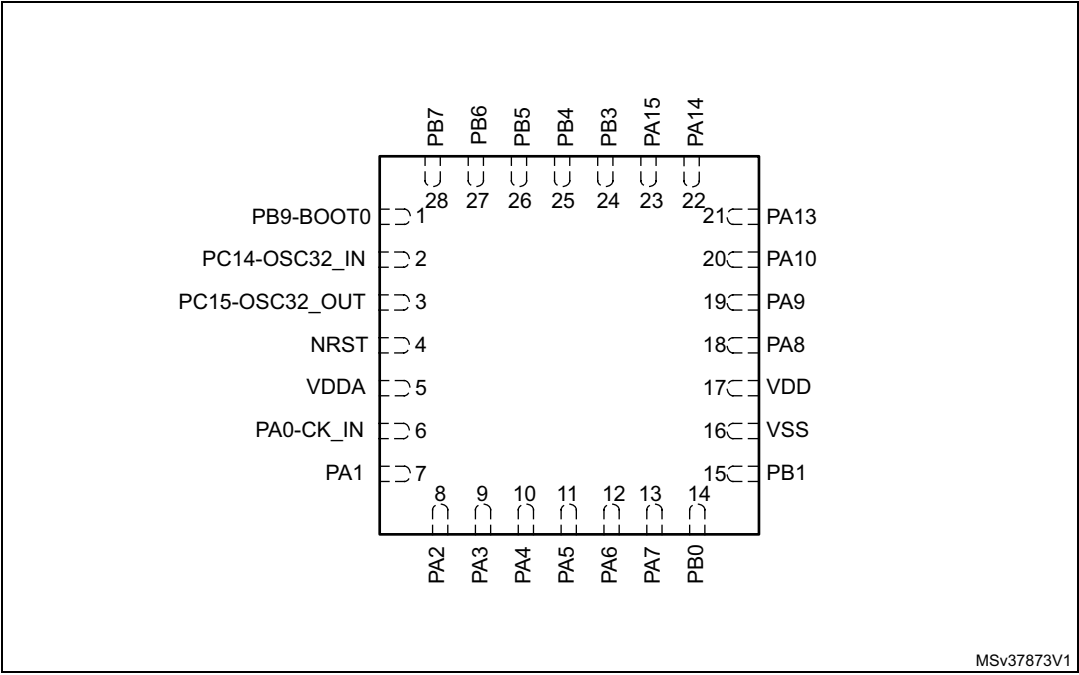
The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (since no external voltage, $V_{\text{REF+}}$, is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area (see [Table 20: Embedded internal reference voltage calibration values](#)). It is accessible in read-only mode.

Figure 5. STM32L011x3/4 WLCSP25 pinout



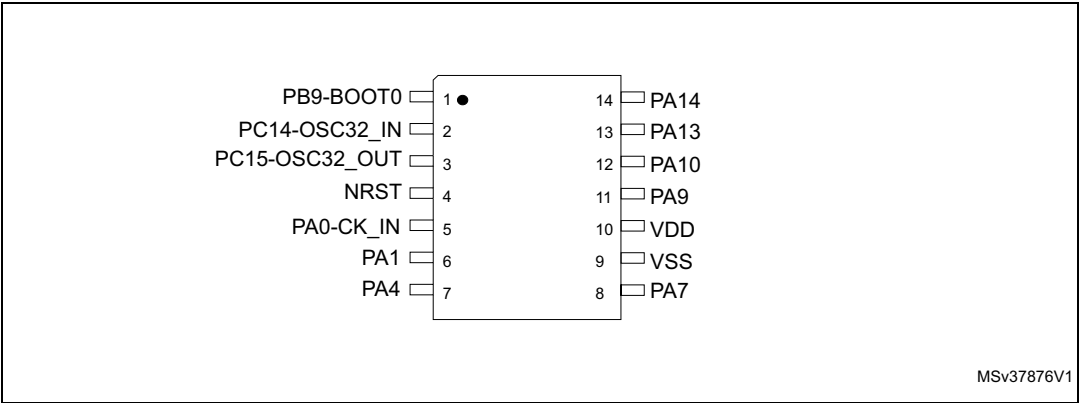
1. The above figure shows the package top view.

Figure 6. STM32L011x3/4 UFQFPN28 pinout



1. The above figure shows the package top view.

Figure 9. STM32L011x3/4 TSSOP14 pinout



1. The above figure shows the package top view.

Table 12. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	FTf	5 V tolerant I/O, FM+ capable
	TTa	3.3 V tolerant I/O directly connected to the ADC
	TC	Standard 3.3V I/O
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers
	Additional functions	Functions directly selected/enabled through peripheral registers

Table 14. Alternate functions

Ports		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/USART2/ TIM21/ EVENTOUT/ SYS_AF	SPI1/I2C1/ LPTIM	LPUART1/ LPTIM/TIM2/ EVENTOUT/ SYS_AF	I2C1/LPTIM/ EVENTOUT	I2C1/USART2/L PUART1/ EVENTOUT	SPI1/TIM2/21	LPUART1/EVE VENTOUT	COMP1/2
Port A	PA0	USART2_RX	LPTIM1_IN1	TIM2_CH1	-	USART2_CTS	TIM2_ETR	LPUART1_RX	COMP1_OUT
	PA1	EVENTOUT	LPTIM1_IN2	TIM2_CH2	I2C1_SMBA	USART2_RTS	TIM21_ETR	LPUART1_TX	-
	PA2	TIM21_CH1	-	TIM2_CH3	-	USART2_TX	-	LPUART1_TX	COMP2_OUT
	PA3	TIM21_CH2	-	TIM2_CH4	-	USART2_RX	-	LPUART1_RX	-
	PA4	SPI1_NSS	LPTIM1_IN1	LPTIM1_ETR	I2C1_SCL	USART2_CK	TIM2_ETR	LPUART1_TX	COMP2_OUT
	PA5	SPI1_SCK	LPTIM1_IN2	TIM2_ETR	-	-	TIM2_CH1	-	-
	PA6	SPI1_MISO	LPTIM1_ETR	-	-	LPUART1_CTS	-	EVENTOUT	COMP1_OUT
	PA7	SPI1_MOSI	LPTIM1_OUT	-	-	USART2_CTS	TIM21_ETR	EVENTOUT	COMP2_OUT
	PA8	MCO	-	LPTIM1_IN1	EVENTOUT	USART2_CK	TIM2_CH1	-	-
	PA9	MCO	I2C1_SCL	LPTIM1_OUT	-	USART2_TX	TIM21_CH2	-	COMP1_OUT
	PA10	TIM21_CH1	I2C1_SDA	RTC_REFIN	-	USART2_RX	TIM2_CH3	-	COMP1_OUT
	PA11	SPI1_MISO	LPTIM1_OUT	EVENTOUT	-	USART2_CTS	TIM21_CH2	-	COMP1_OUT
	PA12	SPI1_MOSI	-	EVENTOUT	-	USART2_RTS	-	-	COMP2_OUT
	PA13	SWDIO	LPTIM1_ETR	-	I2C1_SDA	-	SPI1_SCK	LPUART1_RX	COMP1_OUT
	PA14	SWCLK	LPTIM1_OUT	-	I2C1_SMBA	USART2_TX	SPI1_MISO	LPUART1_TX	COMP2_OUT
	PA15	SPI1_NSS	-	TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	-	-



Table 14. Alternate functions (continued)

Ports		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/USART2/ TIM21/ EVENTOUT/ SYS_AF	SPI1/I2C1/ LPTIM	LPUART1/ LPTIM/TIM2/ EVENTOUT/ SYS_AF	I2C1/LPTIM/ EVENTOUT	I2C1/USART2/L PUART1/ EVENTOUT	SPI1/TIM2/21	LPUART1/EVE VENTOUT	COMP1/2
Port B	PB0	EVENTOUT	SPI1_MISO	TIM2_CH2	-	USART2_RTS	TIM2_CH3	-	-
	PB1	USART2_CK	SPI1_MOSI	LPTIM1_IN1	-	LPUART1_RTS	TIM2_CH4	-	-
	PB2	-	-	LPTIM1_OUT	-	-	-	-	-
	PB3	SPI1_SCK	-	TIM2_CH2	-	EVENTOUT	-	-	-
	PB4	SPI1_MISO	-	EVENTOUT	-	-	-	-	-
	PB5	SPI1_MOSI	-	LPTIM1_IN1	I2C1_SMBA	-	TIM21_CH1	-	-
	PB6	USART2_TX	I2C1_SCL	LPTIM1_ETR	-	-	TIM2_CH3	LPUART1_TX	-
	PB7	USART2_RX	I2C1_SDA	LPTIM1_IN2	-	-	TIM2_CH4	LPUART1_RX	-
	PB8	USART2_TX	-	EVENTOUT	-	I2C1_SCL	SPI1_NSS	-	-
	PB9	-	-	-	-	-	-	-	-
Port C	PC14	-	-	-	-	-	-	-	-
	PC15	-	-	-	-	-	-	-	-

Table 18. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
T _A	Temperature range	Maximum power dissipation (range 6)	-40	85	°C
		Maximum power dissipation (range 7)	-40	105	
		Maximum power dissipation (range 3)	-40	125	
T _J	Junction temperature range (range 6)	-40 °C ≤ T _A ≤ 85 °	-40	105	
	Junction temperature range (range 7)	-40 °C ≤ T _A ≤ 105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤ T _A ≤ 125 °C	-40	130	

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.
2. To sustain a voltage higher than V_{DD}+0.3V, the internal pull-up/pull-down resistors must be disabled.
3. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see [Table 17: Thermal characteristics on page 47](#)).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in [Table 18](#).

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{VDD} ⁽¹⁾	V _{DD} rise time rate	BOR detector enabled	0	-	∞	μs/V
		BOR detector disabled	0	-	1000	
	V _{DD} fall time rate	BOR detector enabled	20	-	∞	
		BOR detector disabled	0	-	1000	
T _{RSTTEMPO} ⁽¹⁾	Reset temporization	V _{DD} rising, BOR enabled	-	2	3.3	ms
		V _{DD} rising, BOR disabled ⁽²⁾	0.4	0.7	1.6	
V _{POR/PDR}	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V _{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
		Rising edge	1.69	1.76	1.8	
V _{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V _{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	

Figure 17. I_{DD} vs V_{DD} , at $T_A = -40/25/55/ 85/105/125\text{ }^{\circ}\text{C}$, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

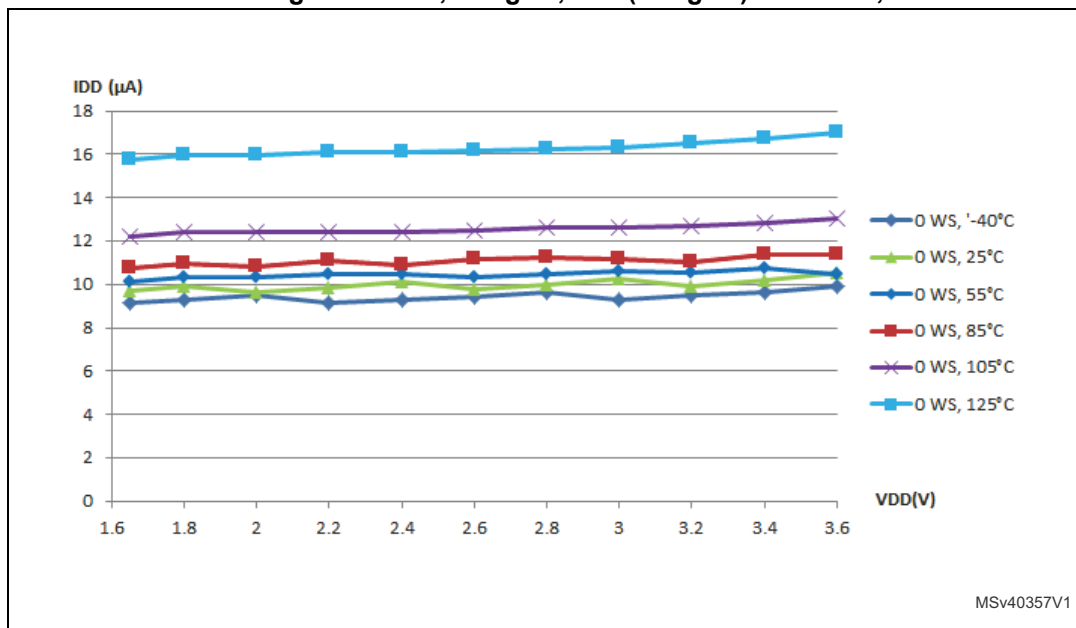


Table 28. Current consumption in Low-power Sleep mode

Symbol	Parameter	Conditions			Typ	Max ⁽¹⁾	Unit
I _{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, V _{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f _{HCLK} = 32 kHz Flash OFF	T _A = -40 °C to 25 °C	2.5 ⁽²⁾	-	μA
			MSI clock, 65 kHz f _{HCLK} = 32 kHz Flash ON	T _A = -40 °C to 25 °C	13	19	
				T _A = 85 °C	15.5	20	
				T _A = 105 °C	17.5	22	
				T _A = 125 °C	21	29	
			MSI clock, 65 kHz f _{HCLK} = 65 kHz, Flash ON	T _A = -40 °C to 25 °C	13.5	19	
				T _A = 85 °C	16	20	
				T _A = 105 °C	18	22	
				T _A = 125 °C	21.5	29	
			MSI clock, 131 kHz f _{HCLK} = 131 kHz, Flash ON	T _A = -40 °C to 25 °C	15.5	21	
				T _A = 55 °C	17	22	
				T _A = 85 °C	18	23	
				T _A = 105 °C	19.5	24	
				T _A = 125 °C	23.5	31	

1. Guaranteed by characterization results at $125\text{ }^{\circ}\text{C}$, not tested in production, unless otherwise specified.

2. As the CPU is in Sleep mode, the difference between the current consumption with Flash memory ON and OFF (nearly $12\text{ }\mu\text{A}$) is the same whatever the clock frequency.

Table 30. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max ⁽¹⁾	Unit
I _{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T _A = -40 °C to 25 °C	0.8	1.6	μA
			T _A = 55 °C	0.9	1.8	
			T _A = 85 °C	1	2	
			T _A = 105 °C	1.25	3	
			T _A = 125 °C	2	7	
		Independent watchdog and LSI OFF	T _A = -40 °C to 25 °C	0.23	0.6	
			T _A = 55 °C	0.25	0.7	
			T _A = 85 °C	0.36	1	
			T _A = 105 °C	0.62	1.7	
			T _A = 125 °C	1.35	5	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified

Table 31. Average current consumption during wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I _{DD} (WU from Stop)	Supply current during wakeup from Stop mode	HSI	1	mA
		HSI/4	0,7	
		MSI 4,2 MHz	0,7	
		MSI 1,05 MHz	0,4	
		MSI 65 KHz	0,1	
I _{DD} (Reset)	Reset pin pulled down	-	0,21	
I _{DD} (Power Up)	BOR ON	-	0,23	
I _{DD} (WU from StandBy)	With Fast wakeup set	MSI 2,1 MHz	0,5	
	With Fast wakeup disabled	MSI 2,1 MHz	0,12	

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked OFF
 - with only one peripheral clocked ON

time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 37. LSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Min ⁽²⁾	Typ	Max	Unit
f_{LSE}	LSE oscillator frequency		-	32.768	-	kHz
G_m	Maximum critical crystal transconductance	LSEDRV[1:0]=00 lower driving capability	-	-	0.5	$\mu A/V$
		LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	
		LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
$t_{SU(LSE)}$ ⁽³⁾	Startup time	V_{DD} is stabilized	-	2	-	s

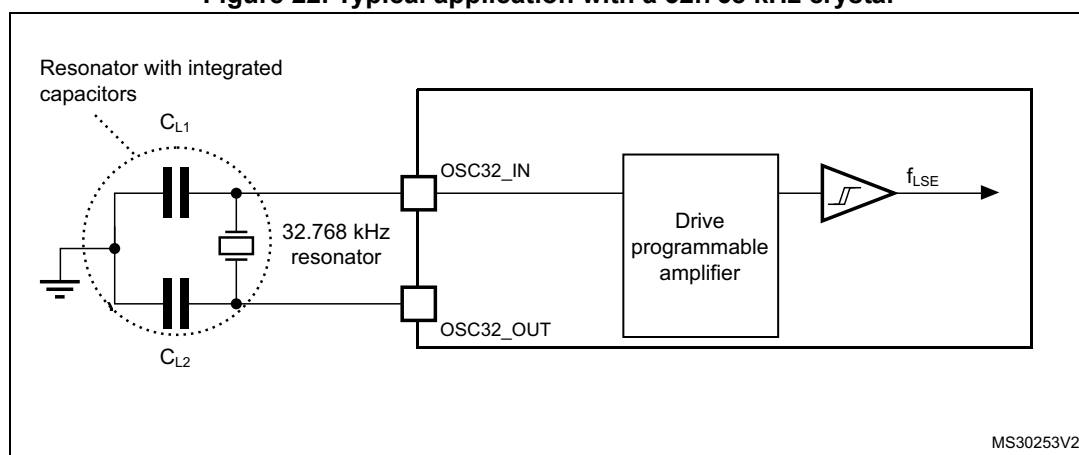
1. Guaranteed by design, not tested in production.

2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

3. Guaranteed by characterization results, not tested in production. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website <http://www.st.com>.

Figure 22. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between $OSC32_IN$ and $OSC32_OUT$ and it is forbidden to add one.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB: A Burst of Fast Transient voltage** (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 45](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 45. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP32, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 32\text{ MHz}$ conforms to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP32, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 32\text{ MHz}$ conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

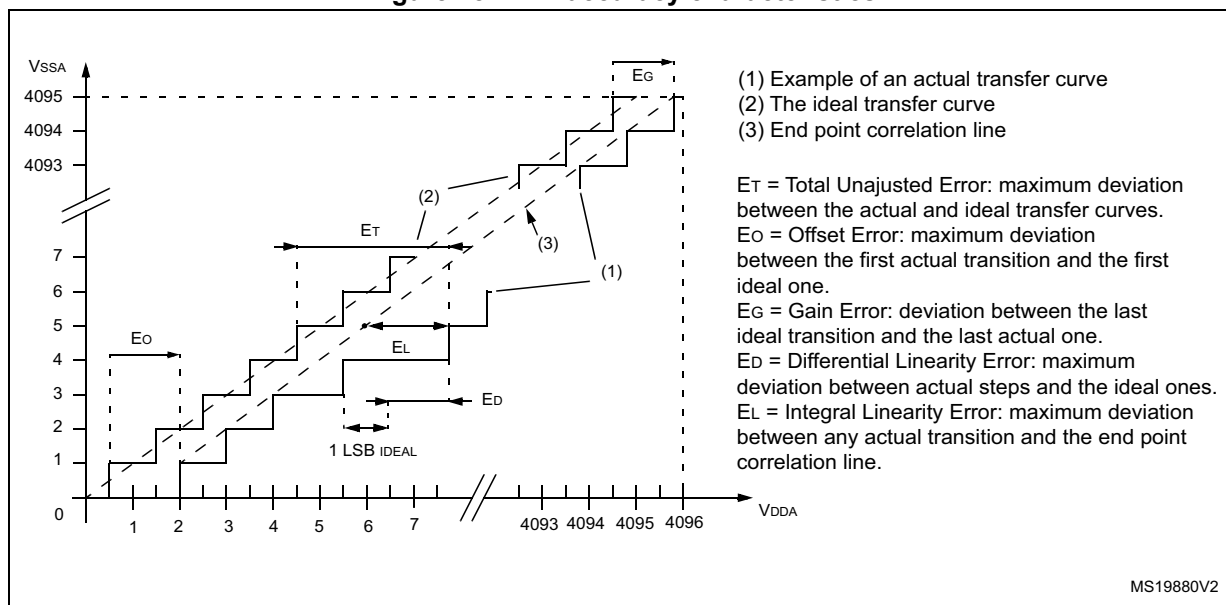
Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

Table 56. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	1.65 V < V _{DDA} < 3.6 V, range 1/2/3, TSSOP14 package	-	3	5	LSB
EO	Offset error		-	2	2.5	
EG	Gain error		-	2	2.5	
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.7	
ENOB	Effective number of bits		9.5	10.5	-	bits
	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁵⁾		10.7	11.6	-	
SINAD	Signal-to-noise distortion		59	65	-	dB
SNR	Signal-to-noise ratio		59	65	-	
	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁵⁾		66	73	-	
THD	Total harmonic distortion		-	-75	-63	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in [Section 6.3.12](#) does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. In TSSOP14 package, where V_{DDA} pin is shared with V_{DD} pin, I/O toggling should be minimized to reach the values given in the above table. I/O toggling with loaded I/O pins can generate ripple on V_{DD}/V_{DDA} and degrade the ADC accuracy.
5. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

Figure 28. ADC accuracy characteristics



SPI characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 18](#).

Refer to [Section 6.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

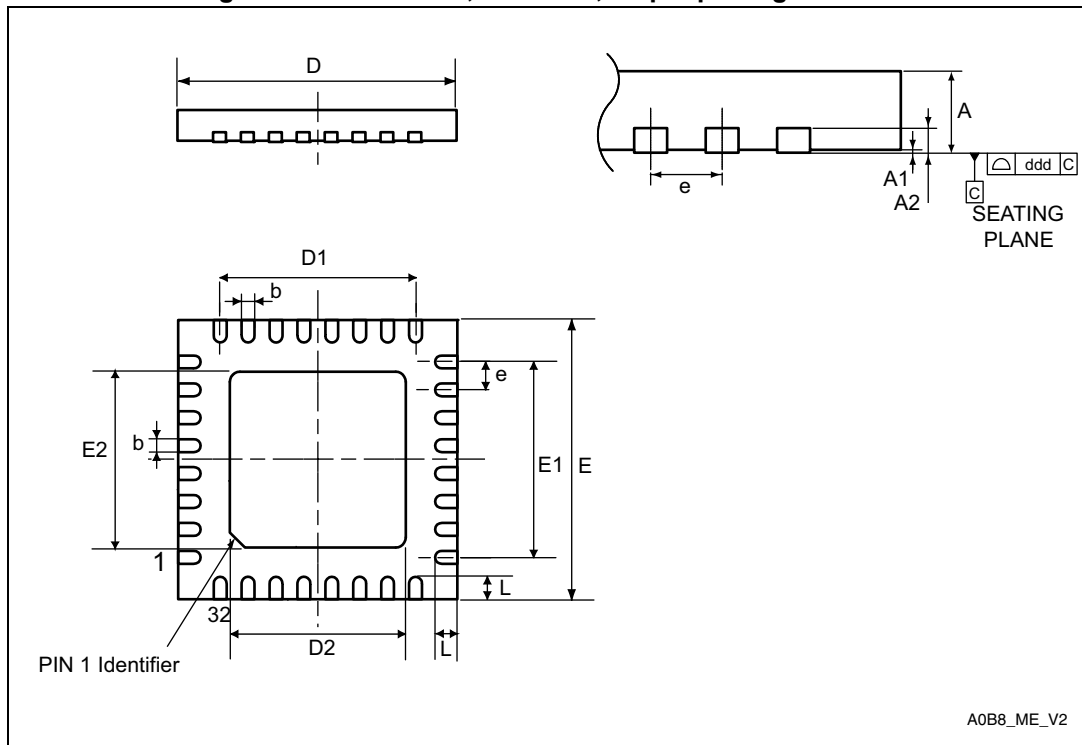
Table 65. SPI characteristics in voltage Range 1 ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	16	MHz
		Slave mode receiver			16	
		Slave mode Transmitter $1.71 < V_{DD} < 3.6V$	-	-	12 ⁽²⁾	
		Slave mode Transmitter $2.7 < V_{DD} < 3.6V$	-	-	16 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4T _{pclk}	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2T _{pclk}	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	T _{pclk} -2	T _{pclk}	T _{pclk} +2	
$t_{su(MI)}$	Data input setup time	Master mode	3	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	3.5	-	-	
$t_{h(SI)}$		Slave mode	0	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	15	-	36	
$t_{dis(SO)}$	Data output disable time	Slave mode	10	-	30	
$t_{v(SO)}$	Data output valid time	Slave mode $1.71 < V_{DD} < 3.6V$	-	14	35	
		Slave mode $2.7 < V_{DD} < 3.6V$	-	14	20	
$t_{v(MO)}$		Master mode	-	4	6	
$t_{h(SO)}$	Data output hold time	Slave mode	10	-	-	
$t_{h(MO)}$		Master mode	3	-	-	

1. Guaranteed by characterization results, not tested in production.
2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty_(SCK) = 50%.

7.2 UFQFPN32 package information

Figure 36. UFQFPN32, 5 x 5 mm, 32-pin package outline



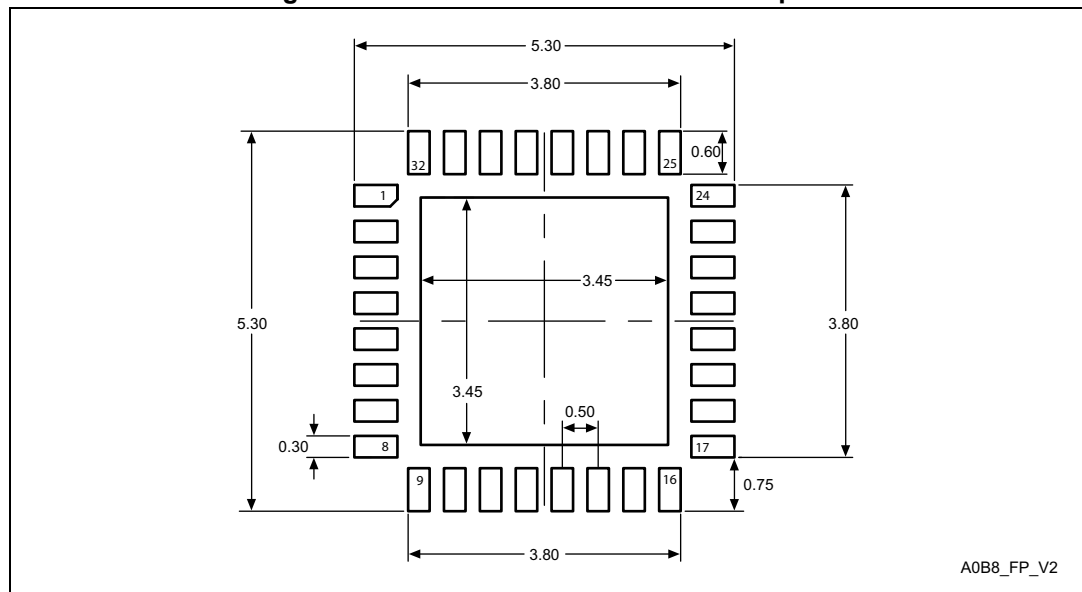
1. Drawing is not to scale.

Table 69. UFQFPN32, 5 x 5 mm, 32-pin package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.200	-	-	0.0079	-
b	0.180	0.250	0.300	0.0071	0.0098	0.0118
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D2	3.200	3.450	3.700	0.1260	0.1358	0.1457
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E2	3.200	3.450	3.700	0.1260	0.1358	0.1457
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 37. UFQFPN32 recommended footprint

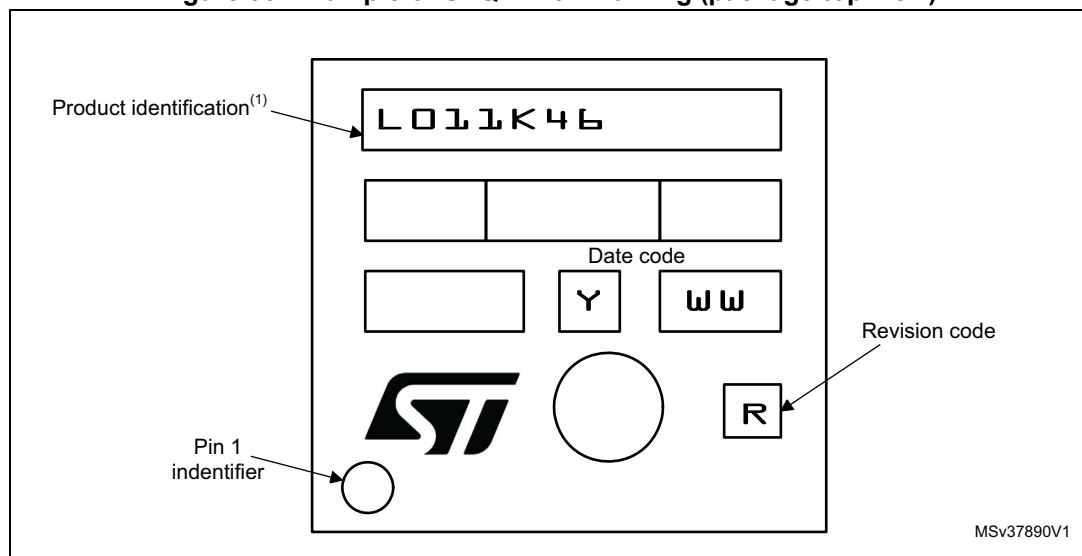


1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

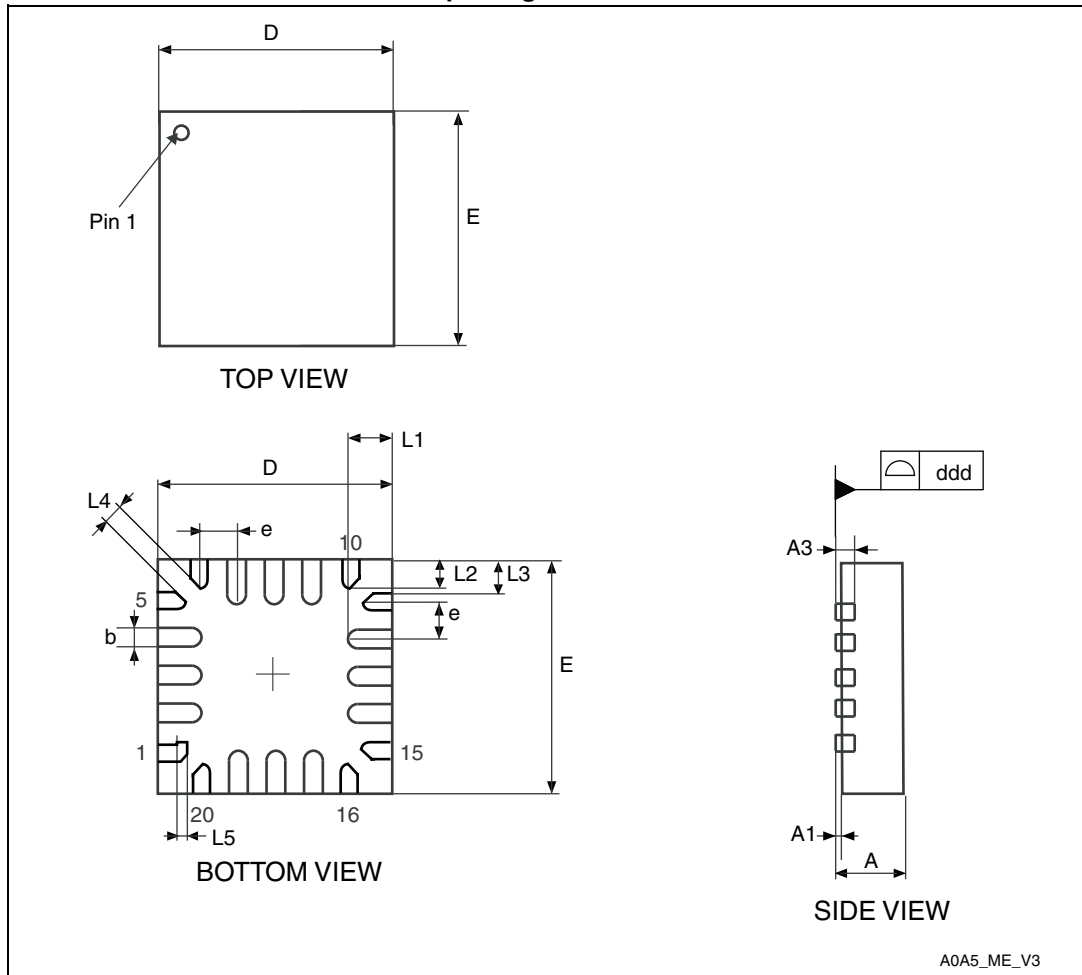
Figure 38. Example of UFQFPN32 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.5 UFQFPN20 package information

Figure 45. UFQFPN20 - 20-lead, 3x3 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline



1. Drawing is not to scale.

8 Part numbering

Table 77. STM32L011x3/4 ordering information scheme

Example:	STM32	L	011	K	4	T	6	D	xxx									
Device family																		
STM32 = ARM-based 32-bit microcontroller																		
Product type																		
L = Low power																		
Device subfamily																		
011 = Access line																		
Pin count																		
K = 32 pins																		
G = 28 pins																		
E = 25 pins																		
F = 20 pins																		
D = 14 pins																		
Flash memory size																		
3 = 8 Kbytes																		
4 = 16 Kbytes																		
Package																		
T = LQFP																		
U = UFQFPN																		
Y = WLCSP																		
P = TSSOP																		
Temperature range																		
6 = Industrial temperature range, −40 to 85 °C																		
7 = Industrial temperature range, −40 to 105 °C																		
3 = Industrial temperature range, −40 to 125 °C																		
Options																		
No character = V _{DD} range: 1.8 to 3.6 V and BOR enabled																		
D = V _{DD} range: 1.65 to 3.6 V and BOR disabled																		
Packing																		
TR = tape and reel																		
No character = tray or tube																		

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

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